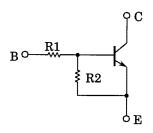
TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

RN1107F,RN1108F,RN1109F

Switching, Inverter Circuit, Interface Circuit And Driver Circuit Applications

- With built-in bias resistors.
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process
- Complementary to RN2107F~2109F

Equivalent Circuit and Bias Resistor Values



| Type No. | R1 (kΩ) | R2 (kΩ) |
|----------|---------|---------|
| RN1107F | 10 | 47 |
| RN1108F | 22 | 47 |
| RN1109F | 47 | 22 |

1. BASE 2. EMITTER 3. COLLECTOR JEDEC — EIAJ — TOSHIBA 2-2HA1A

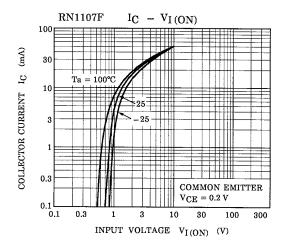
Maximum Ratings (Ta = 25°C)

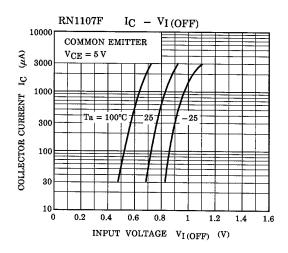
| Characterist | Symbol | Rating | Unit | | |
|-----------------------------|---------------|------------------|---------|----|--|
| Collector-base voltage | RN1107F~1109F | V_{CBO} | 50 | V | |
| Collector-emitter voltage | RN1107F~1109F | V_{CEO} | 50 | V | |
| | RN1107F | | 6 | ٧ | |
| Emitter-base voltage | RN1108F | V_{EBO} | 7 | | |
| | RN1109F | | 15 | | |
| Collector current | RN1107F~1109F | Ic | 100 | mA | |
| Collector power dissipation | RN1107F~1109F | Pc | 100 | mW | |
| Junction temperature | RN1107F~1109F | Tj | 150 | °C | |
| Storage temperature range | RN1107F~1109F | T _{stg} | -55~150 | °C | |

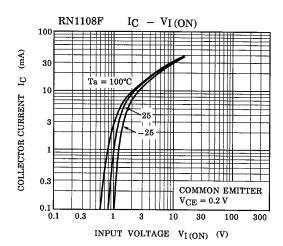


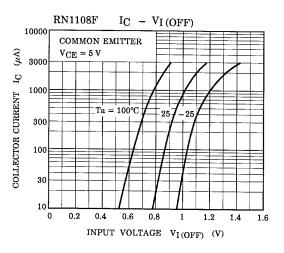
Electrical Characteristics (Ta = 25°C)

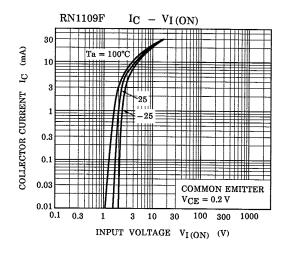
| Character | ristic | Symbol | Test Circuit | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------------|----------------|-----------------------|-----------------|--|-------|-------|-------|------|
| Collector cut-off current | RN1107F~1109F | I _{CBO} | _ | V _{CB} = 50V, I _E = 0 | _ | _ | 100 | nA |
| | KN1107F-21109F | I _{CEO} | _ | V _{CE} = 50V, I _B = 0 | _ | _ | 500 | nA |
| | RN1107F | | _ | V _{EB} = 6V, I _C = 0 | 0.081 | _ | 0.15 | |
| Emitter cut-off current | RN1108F | I _{EBO} | _ | V _{EB} = 7V, I _C = 0 | 0.078 | _ | 0.145 | mA |
| | RN1109F | | _ | V _{EB} = 15V, I _C = 0 | 0.167 | _ | 0.311 | |
| | RN1107F | | _ | | 80 | _ | _ | |
| DC current gain | RN1108F | h _{FE} | _ | V _{CE} = 5V, I _C = 10mA | 80 | _ | _ | _ |
| | RN1109F | | _ | | 70 | _ | _ | |
| Collector-emitter saturation voltage | RN1107F~1109F | V _{CE} (sat) | _ | I _C = 5mA, I _B = 0.25mA | _ | 0.1 | 0.3 | V |
| | RN1107F | | _ | | 0.7 | _ | 1.8 | |
| Input voltage (ON) | RN1108F | V _{I (ON)} | _ | V _{CE} = 0.2V, I _C = 5mA | 1.0 | _ | 2.6 | V |
| | RN1109F | | _ | | 2.2 | _ | 5.8 | |
| | RN1107F | | _ | | 0.5 | _ | 1.0 | |
| Input voltage (OFF) | RN1108F | V _{I (OFF)} | _ | V _{CE} = 5V, I _C = 0.1mA | 0.6 | _ | 1.16 | V |
| | RN1109F | | _ | | 1.5 | _ | 2.6 | |
| Translation frequency | RN1107F~1109F | f _T | _ | V _{CE} =10V, I _C = 5mA | _ | 250 | - | MHz |
| Collector output capacitance | RN1107F~1109F | C _{ob} | _ | V _{CB} = 10V, I _E = 0, f = 1MHz | _ | 3 | 6 | pF |
| | RN1107F | | _ | | 7 | 10 | 13 | |
| Input Resistor | RN1108F | R1 | _ | _ | 15.4 | 22 | 28.6 | kΩ |
| | RN1109F | | _ | | 32.9 | 47 | 61.1 | |
| | RN1107F | | _ | | 0.191 | 0.213 | 0.232 | |
| Resistor Ratio | RN1108F | R1/R2 | _ | _ | 0.421 | 0.468 | 0.515 | _ |
| | RN1109F | | _ | | 1.92 | 2.14 | 2.35 | |

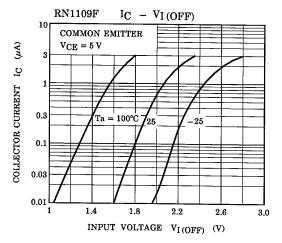


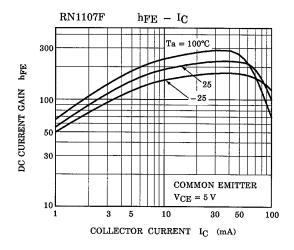


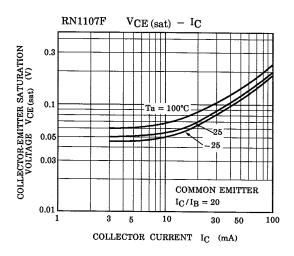


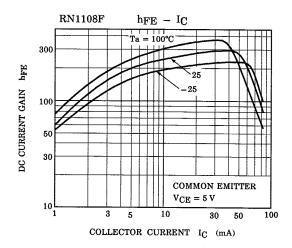


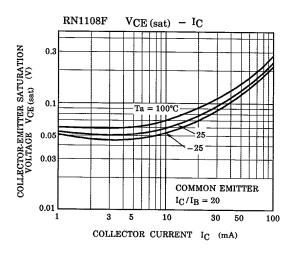


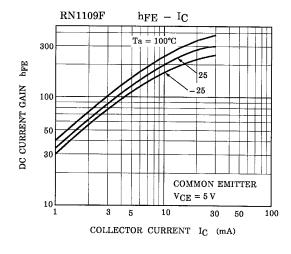


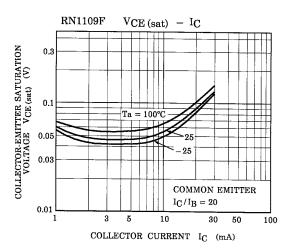












| Type Name | Marking |
|-----------|----------------|
| RN1107F | Type Name X H |
| RN1108F | Type Name |
| RN1109F | Type Name |

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000707EAA

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